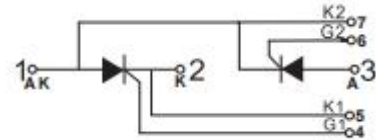


**FEATURES**

- Long-term stability
- Low Leakage Current
- Base plate: Copper
- Minimum Lot-to-Lot variations for robust device performance and reliable operation


**ABSOLUTE MAXIMUM RATINGS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{RRM}$ $V_{DRM}$	Repetitive Peak Reverse Voltage Repetitive Peak Forward Blocking Voltage		1600	V
$I_{T(AV)}$	Average on-state current	sin. 180; $T_c = 85(100)^{\circ}C$	150	A
$I_{TSM}$	Peak, One-cycle, Non-repetitive Surge Current	$T_{vj} = 25^{\circ}C$ ; 10ms	5400	A
		$T_{vj} = 125^{\circ}C$ ; 10ms	5000	
$I^2t$	For Fusing	$T_{vj} = 25^{\circ}C$ ; 8, 3 ...10ms	1450	KA <sup>2</sup> S
		$T_{vj} = 125^{\circ}C$ ; 8, 3 ...10ms	125	
$V_{iso}$	isolation voltage	a. c. 50Hz; r.m.s. ; 1s/1min	3600/3000	V~
$T_J$	Junction Temperature		-40~125	$^{\circ}C$
$T_{stg}$	Storage Temperature Range		-40~125	$^{\circ}C$

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	per thyristor / per module	0.17/0.085	K/W

